# NSS12501UW3T2G

# 12 V, 7.0 A, Low $V_{CE(sat)}$ NPN Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

- This is a Pb-Free Device

### MAXIMUM RATINGS ($T_A$ = 25°C)

| Rating | Symbol | Max | Unit |
|---|---|---|---|
| Collector-Emitter Voltage | $V_{CEO}$ | 12 | Vdc |
| Collector-Base Voltage | $V_{CBO}$ | 12 | Vdc |
| Emitter-Base Voltage | $V_{EBO}$ | 6.0 | Vdc |
| Collector Current - Continuous | $I_C$ | 5.0 | Adc |
| Collector Current - Peak | $I_{CM}$ | 7.0 | A |
| Electrostatic Discharge | ESD | HBM Class 3B<br>MM Class C | |

### THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|---|---|---|
| Total Device Dissipation, $T_A$ = 25°C<br>Derate above 25°C | $P_D$ (Note 1) | 875<br>7.0 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction-to-Ambient | $R_{\theta JA}$ (Note 1) | 143 | °C/W |
| Total Device Dissipation, $T_A$ = 25°C<br>Derate above 25°C | $P_D$ (Note 2) | 1.5<br>11.8 | W<br>mW/°C |
| Thermal Resistance,<br>Junction-to-Ambient | $R_{\theta JA}$ (Note 2) | 85 | °C/W |
| Thermal Resistance,<br>Junction-to-Lead #1 | $R_{\theta JL}$ (Note 2) | 23 | °C/W |
| Junction and Storage<br>Temperature Range | $T_J$, $T_{stg}$ | -55 to<br>+150 | °C |

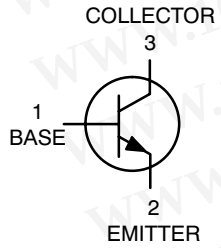
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

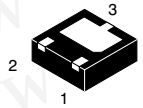
1. FR-4 @ 100 mm², 1 oz copper traces.
2. FR-4 @ 500 mm², 1 oz copper traces.

**ON Semiconductor®**

**http://onsemi.com**

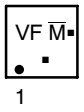
## 12 VOLTS, 7.0 AMPS
## NPN LOW $V_{CE(sat)}$ TRANSISTOR
## EQUIVALENT $R_{DS(on)}$ 31 mΩ




**WDFN3**
**CASE 506AU**

### MARKING DIAGRAM




VF = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| NSS12501UW3T2G | WDFN3<br>(Pb-Free) | 3000/<br>Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**ELECTRICAL CHARACTERISTICS** ($T_A$ = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typical | Max | Unit |
|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | |
| Collector-Emitter Breakdown Voltage ($I_C$ = 10 mAdc, $I_B$ = 0) | $V_{(BR)CEO}$ | 12 | - | - | Vdc |
| Collector-Base Breakdown Voltage ($I_C$ = 0.1 mAdc, $I_E$ = 0) | $V_{(BR)CBO}$ | 12 | - | - | Vdc |
| Emitter-Base Breakdown Voltage ($I_E$ = 0.1 mAdc, $I_C$ = 0) | $V_{(BR)EBO}$ | 6.0 | - | - | Vdc |
| Collector Cutoff Current ($V_{CB}$ = 12 Vdc, $I_E$ = 0) | $I_{CBO}$ | - | - | 0.1 | μAdc |
| Emitter Cutoff Current ($V_{EB}$ = 6.0 Vdc) | $I_{EBO}$ | - | - | 0.1 | μAdc |
| **ON CHARACTERISTICS** | | | | | |
| DC Current Gain (Note 3)<br>($I_C$ = 10 mA, $V_{CE}$ = 2.0 V)<br>($I_C$ = 500 mA, $V_{CE}$ = 2.0 V)<br>($I_C$ = 1.0 A, $V_{CE}$ = 2.0 V)<br>($I_C$ = 2.0 A, $V_{CE}$ = 2.0 V)<br>($I_C$ = 3.0 A, $V_{CE}$ = 2.0 V) | $h_{FE}$ | <br>200<br>200<br>200<br>200<br>200 | <br>-<br>-<br>345<br>330<br>315 | <br>-<br>-<br>-<br>-<br>- | |
| Collector-Emitter Saturation Voltage (Note 3)<br>($I_C$ = 0.1 A, $I_B$ = 0.010 A)<br>($I_C$ = 1.0 A, $I_B$ = 0.100 A)<br>($I_C$ = 1.0 A, $I_B$ = 0.010 A)<br>($I_C$ = 2.0 A, $I_B$ = 0.020 A)<br>($I_C$ = 3.0 A, $I_B$ = 0.030 A)<br>($I_C$ = 4.0 A, $I_B$ = 0.400 A) | $V_{CE(sat)}$ | <br>-<br>-<br>-<br>-<br>-<br>- | <br>0.007<br>0.031<br>0.045<br>0.070<br>0.100<br>0.100 | <br>0.008<br>0.035<br>0.060<br>0.100<br>0.120<br>0.120 | V |
| Base-Emitter Saturation Voltage (Note 3) ($I_C$ = 1.0 A, $I_B$ = 0.01 A) | $V_{BE(sat)}$ | - | 0.760 | 0.900 | V |
| Base-Emitter Turn-on Voltage (Note 3) ($I_C$ = 2.0 A, $V_{CE}$ = 2.0 V) | $V_{BE(on)}$ | - | 0.730 | 0.900 | V |
| Cutoff Frequency ($I_C$ = 100 mA, $V_{CE}$ = 5.0 V, f = 100 MHz) | $f_T$ | 150 | - | - | MHz |
| Input Capacitance ($V_{EB}$ = 0.5 V, f = 1.0 MHz) | Cibo | - | | 650 | pF |
| Output Capacitance ($V_{CB}$ = 3.0 V, f = 1.0 MHz) | Cobo | - | | 120 | pF |
| **SWITCHING CHARACTERISTICS** | | | | | |
| Delay ($V_{CC}$ = 10 V, $I_C$ = 750 mA, $I_{B1}$ = 15 mA) | $t_d$ | - | - | 90 | ns |
| Rise ($V_{CC}$ = 10 V, $I_C$ = 750 mA, $I_{B1}$ = 15 mA) | $t_r$ | - | - | 100 | ns |
| Storage ($V_{CC}$ = 10 V, $I_C$ = 750 mA, $I_{B1}$ = 15 mA) | $t_s$ | - | - | 320 | ns |
| Fall ($V_{CC}$ = 10 V, $I_C$ = 750 mA, $I_{B1}$ = 15 mA) | $t_f$ | - | - | 100 | ns |

3. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%.

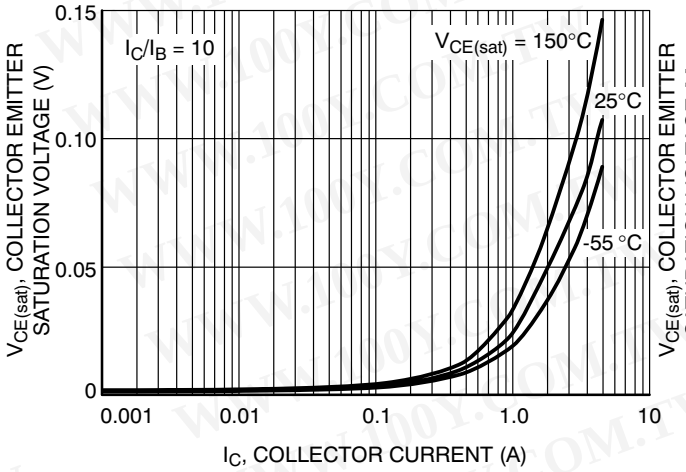



**Figure 1. Collector Emitter Saturation Voltage vs. Collector Current**

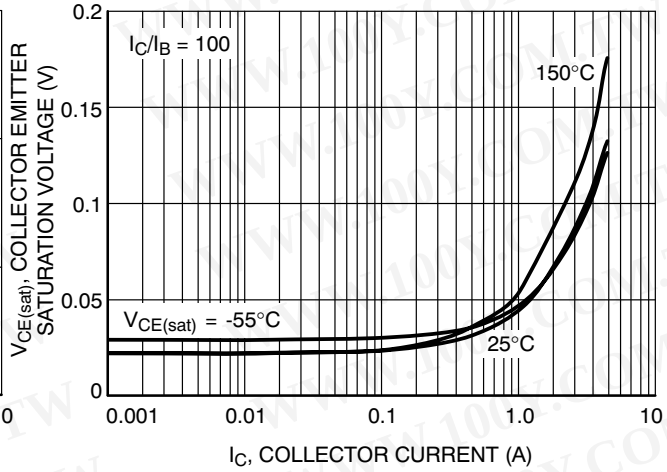



**Figure 2. Collector Emitter Saturation Voltage vs. Collector Current**

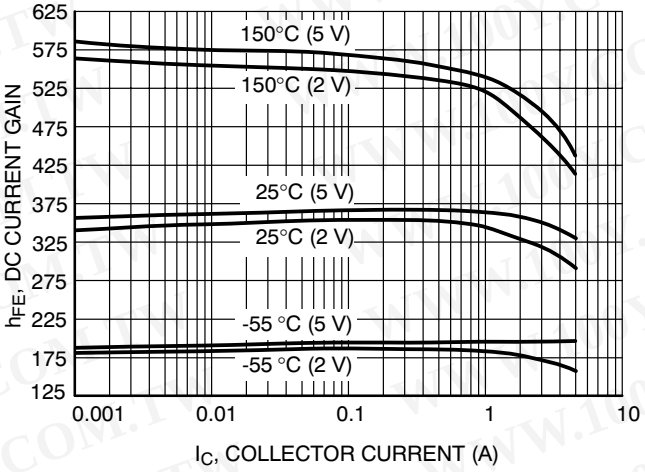



**Figure 3. DC Current Gain vs. Collector Current**

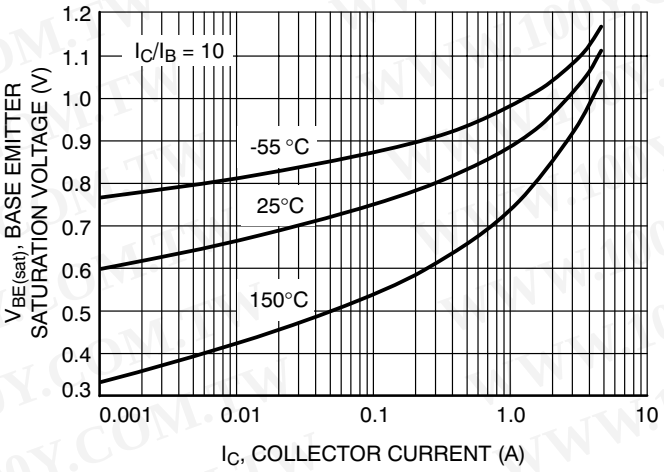



**Figure 4. Base Emitter Saturation Voltage vs. Collector Current**

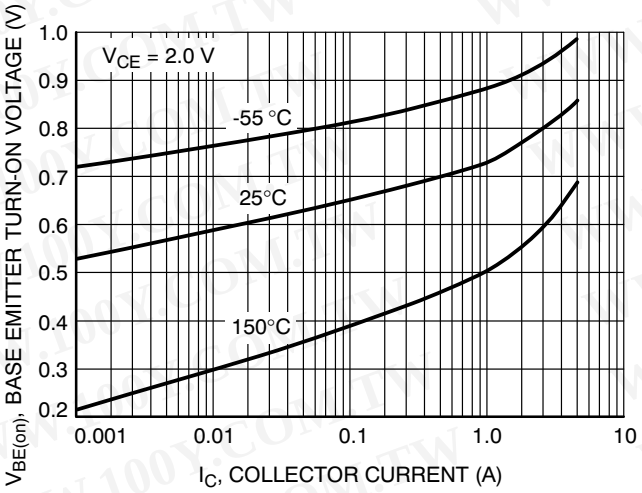



**Figure 5. Base Emitter Turn-On Voltage vs. Collector Current**

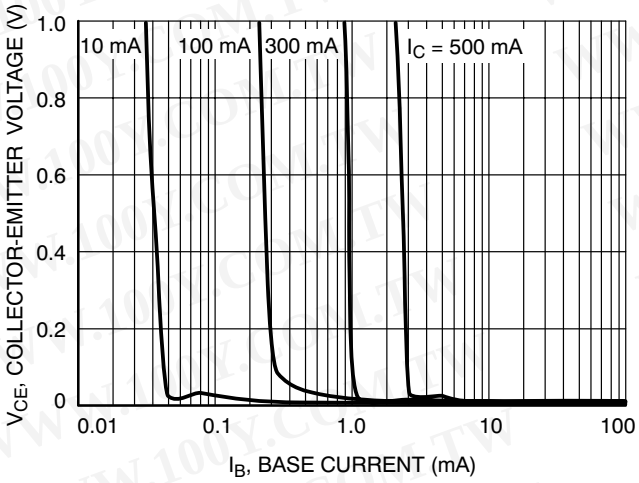



**Figure 6. Saturation Region**

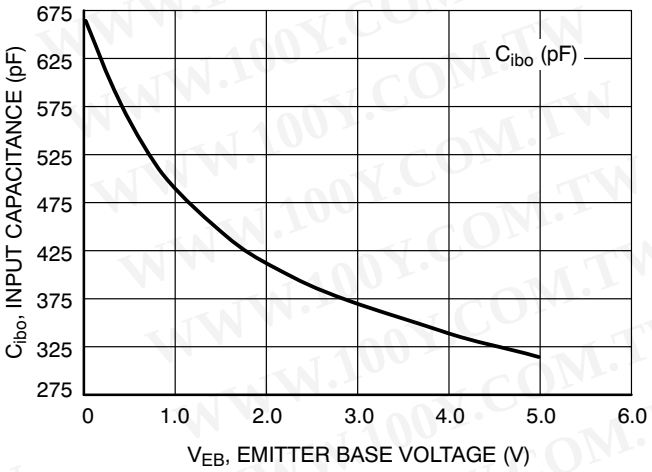



**Figure 7. Input Capacitance**

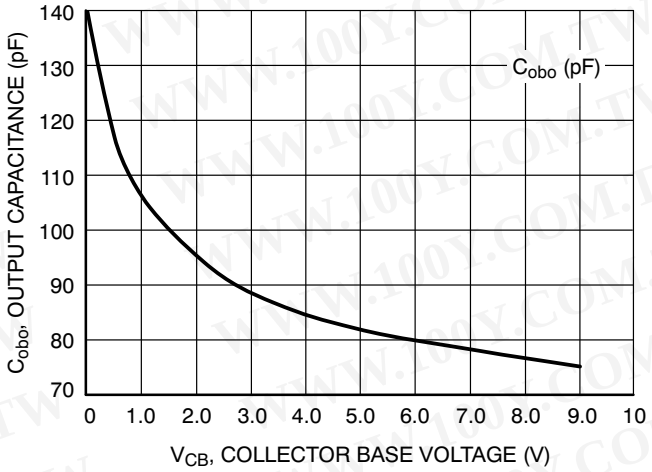



**Figure 8. Output Capacitance**

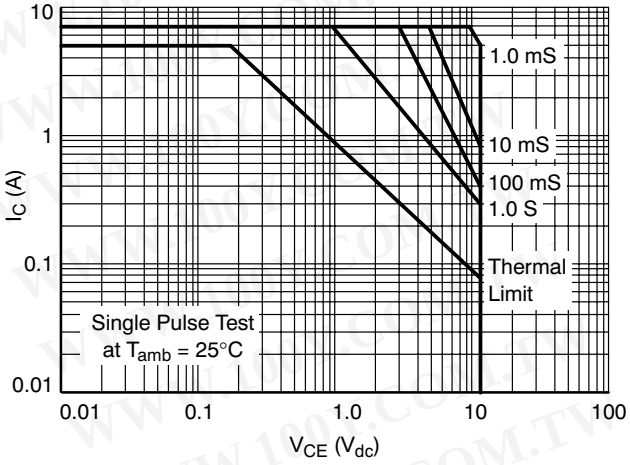
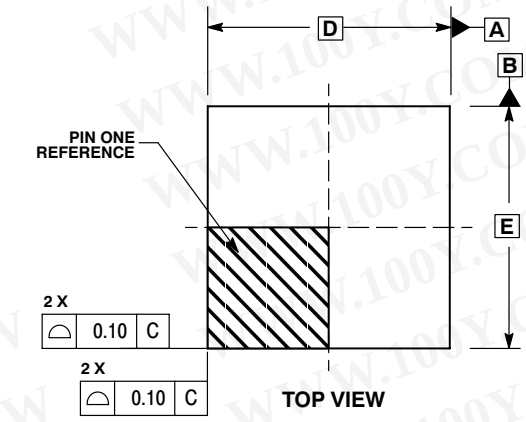



**Figure 9. Safe Operating Area**

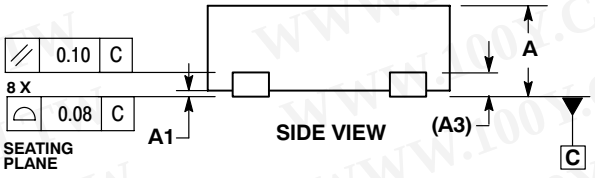
# NSS12501UW3T2G

## PACKAGE DIMENSIONS

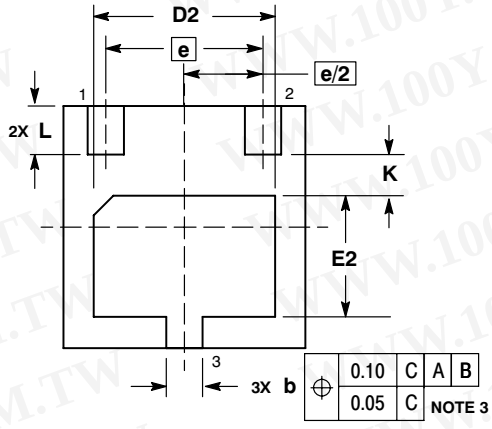
**WDFN3**
CASE 506AU-01
ISSUE O




TOP VIEW




SIDE VIEW

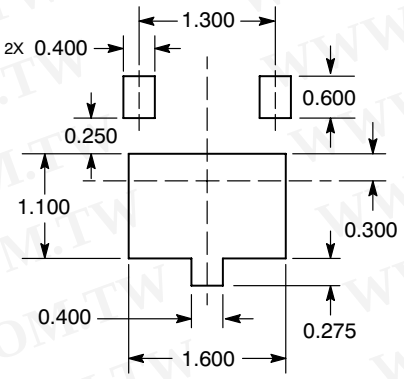



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

| | MILLIMETERS | | | INCHES | | |
|---|---|---|---|---|---|---|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 | 0.028 | 0.030 | 0.031 |
| A1 | 0.00 | | 0.05 | 0.000 | | 0.002 |
| A3 | | 0.20 REF | | | 0.008 REF | |
| b | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| D | | 2.00 BSC | | | 0.079 BSC | |
| D2 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| E | | 2.00 BSC | | | 0.079 BSC | |
| E2 | 0.90 | 1.00 | 1.10 | 0.035 | 0.039 | 0.043 |
| e | | 1.30 BSC | | | 0.051 BSC | |
| K | | 0.35 REF | | | 0.014 REF | |
| L | 0.35 | 0.40 | 0.45 | 0.014 | 0.016 | 0.018 |

### SOLDERING FOOTPRINT*




*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





### PUBLICATION ORDERING INFORMATION


**LITERATURE FULFILLMENT**:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
**Phone**: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
**Fax**: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
**Email**: orderlit@onsemi.com

**N. American Technical Support**: 800-282-9855 Toll Free USA/Canada
**Europe, Middle East and Africa Technical Support:**
Phone: 421 33 790 2910
**Japan Customer Focus Center**
Phone: 81-3-5773-3850

**ON Semiconductor Website**: **www.onsemi.com**

**Order Literature**: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative